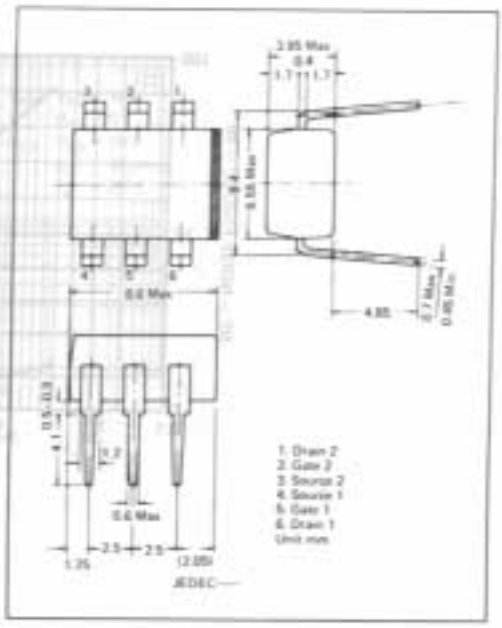
2SK58

Silicon N-Channel Junction Type Dual FET

- DC-to-VHF Use, Low Noise,
- オーディオプリアンプ，パワーアンプ初段，オシロスコープ
- Oscilloscope, Oscillators, Audio Pre-Amplifiers
- Head-Amplifiers of Audio Power Amplifiers
- Single Type: 2SK23A
  2SK107 (Economical Type)



絶対最大定格 Absolute Maximum Ratings $T_a = 25°C$

Characteristics	Symbol	2SK58
Drain-to-Gate Voltage	V_{DGO}	27 V
Source-to-Gate Voltage	V_{SGO}	9 V
Drain Current	I_D	20 mA (1 FET)
Gate Current	I_G	10 mA (1 FET)
Total Power Dissipation	P_T	270 mW (2 FET)
Channel Temperature	T_{ch}	100°C
Storage Temperature	T_{stg}	-30—+120°C

電気的特性 Electrical Characteristics $T_a = 25°C$

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-to-Gate Voltage	V_{DGO}	$I_{DG} = 10\mu A$	27			V
Source-to-Gate Voltage	V_{SGO}	$I_{SG} = 10\mu A$	9			V
Forward Transfer Conductance	g_m	$V_{DS} = 10V$, $V_{GS} = 0V$, f = 1 kHz	2.7			m℧
Gate Cutoff Current	I_{GSS}	$V_{GS} = -6V$, $V_{DS} = 0$		-0.05	-10	nA
Drain Saturation Current	I_{DSS}	$V_{DS} = 10V$, $V_{GS} = 0$	1.0		16.5	mA
Pinch-off Voltage	V_p	$V_{DS} = 10V$, $I_D = 30\mu A$	-0.45		-4.95	V
Reverse Transfer Capacitance	C_{dg}	$V_{DS} = 10V$, f = 1 MHz		2.0		pF
V_{GS} Difference between Two FETs	ΔV_{GS}	$V_{DS} = 10V$, $I_D = 1mA$			100	mV
Drain Cutoff Current	I_{DGO}	$V_{DG} = 20V$			15	nA